

Silicon NPN Power Transistors

2SC1102

DESCRIPTION

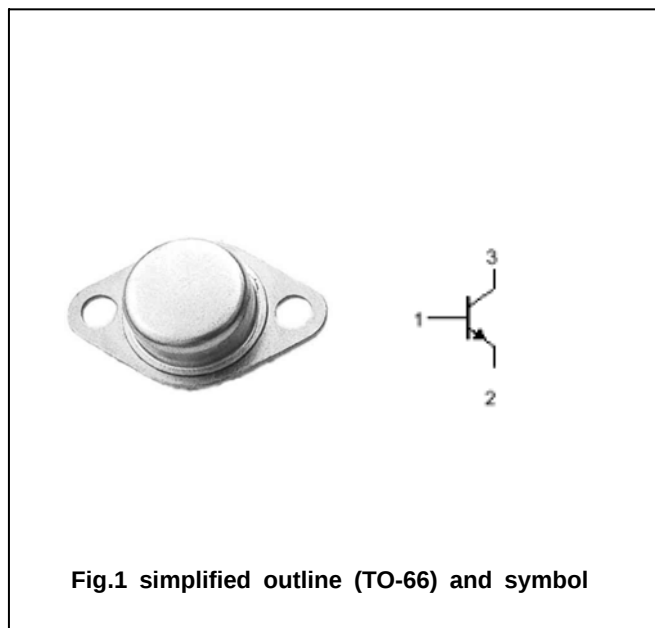
- With TO-66 package
- High voltage
- High transition frequency

APPLICATIONS

- For color TV video output applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		50	mA
P_T	Total power dissipation	$T_C=25^{\circ}\text{C}$	11	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

Silicon NPN Power Transistors**2SC1102****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1mA ; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1 μ A; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =20mA; I _B =2mA			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =20mA; I _B =2mA			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =200V; I _B =0			1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	μ A
h _{FE}	DC current gain	I _C =10mA ; V _{CE} =10V	40		200	
f _T	Transition frequency	I _C =10mA ; V _{CE} =20V	60			MHz

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PACKAGE OUTLINE

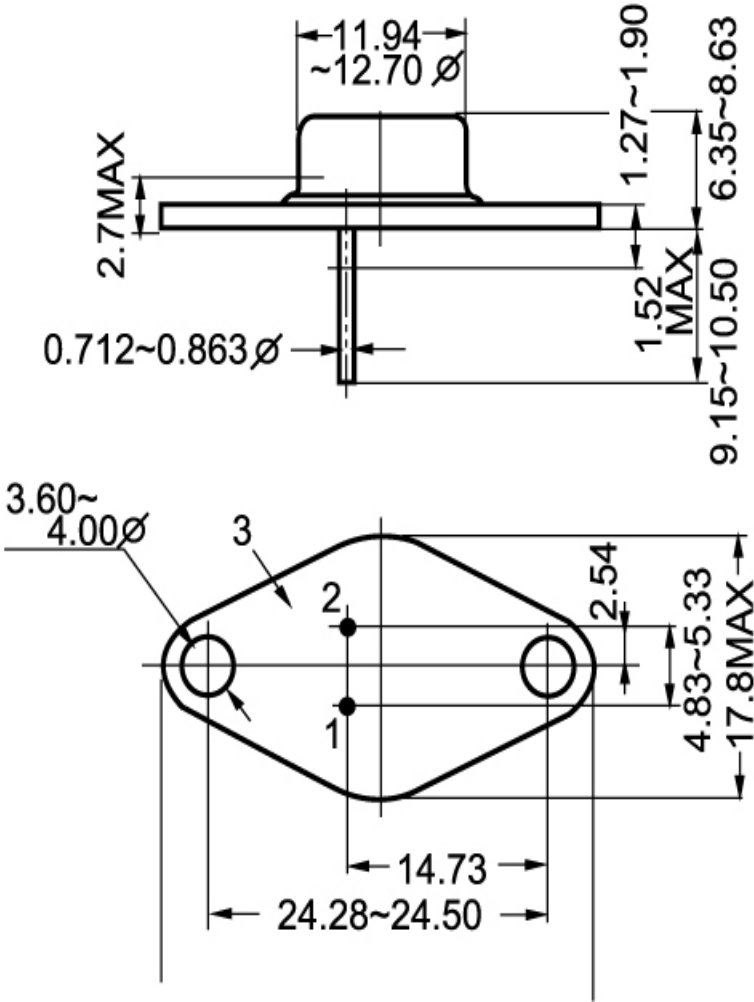


Fig.2 Outline dimensions